



BSPE80S120HN

General Description

概述

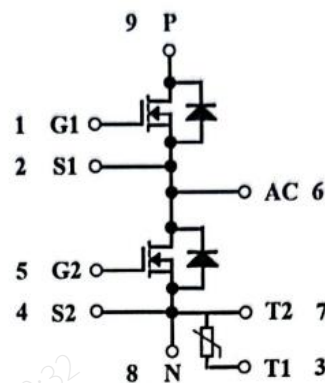
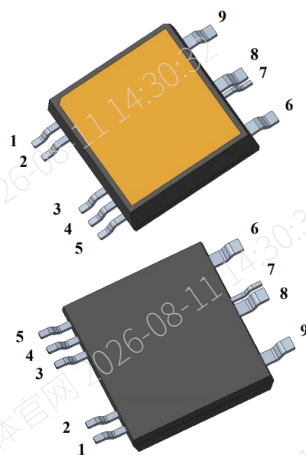
Specifically designed for Automotive applications, this SiC Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per unit area.

本产品是一款专为汽车应用设计的碳化硅功率MOSFET产品，采用了先进的工艺技术，产品的单位面积导通电阻低。

Features

特点

- High Speed Switching with Low Capacitances
开关速度快，寄生电容小
- High Blocking Voltage with Low $R_{DS(on)}$
阻断电压高，开通电阻低
- 100% avalanche tested
100%通过雪崩测试
- Halogen Free and RoHS Compliant
无卤元素，符合 RoHS



Typical Applications

典型应用

- Solar Inverters
太阳能逆变器
- EV motor drive
EV 电机驱动
- High Voltage DC/DC Converters
高压 DC/DC 变压器
- Switched mode power supplies
开关模式电源

Ordering Information

订货信息

Type 型号	$BV_{DSS}[V]$ 漏极-源极电压	$R_{DS(on)}[m\Omega]$ 导通电阻	$T_{jmax}[^{\circ}C]$ 最高结温	Marking 标记	Packing 封装外形
BSPE80S120HN	1200	80	175	80S120HN	SOP9



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Maximum Rated Values

最大额定参数

Parameter 参数	Symbol 符号	Value 数值	Unit 单位
Drain-Source Voltage, $T_j \geq 25^\circ\text{C}$ 漏-源电压, $T_j \geq 25^\circ\text{C}$	V_{DSS}	1200	V
Drain Current(continuous)at $T_c=25^\circ\text{C}$ 常温下漏极电流(持续)	I_{D}	34	A
Drain Current(continuous)at $T_c=100^\circ\text{C}$ $T_c=100^\circ\text{C}$ 下漏极电流(持续)		24	
Pulsed Drain current, t_p limited by $T_{j \max}$ 集电极脉冲电流, 脉宽时间受 $T_{j \max}$ 限制	I_{DM}	80	
Gate-Source Voltage 栅极-源极电压	V_{GSmax}	-10/+22	V
Gate-Source Voltage (Recommended operational values) 栅极-源极电压(推荐工作电压)	V_{GSop}	-5/+18	V
Power Dissipation $T_c = 25^\circ\text{C}$ 常温耗散功率	P_{D}	176	W
Storage Temperature Range 储存温度范围	T_{stg}	-55 to +175	$^\circ\text{C}$
Operating junction temperature Range 工作结温	T_j		
Solder Temperature, 1.6mm case from for10s 焊接温度	T_L	260	

Caution: These values must not be exceeded under any conditions.

注意：任何条件下都不能超出上述值。

Thermal Resistance

热阻

Parameter 参数	Symbol 符号	Value 值	Unit 单位
Thermal Resistance, Junction to Case, Max. 结-管壳热阻	$R_{\theta \text{JC}}$	0.85	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient, Max. 结-环境热阻	$R_{\theta \text{JA}}$	40	

***BSPE80S120HN*****Electrical Characteristic at $T_j = 25^\circ\text{C}$ (unless otherwise specified)** **$T_j=25^\circ\text{C}$ 时电学特性（除非特别声明）**

Parameter 参数	Symbol 符号	Conditions 条件	Value 值			Unit 单位
			Min. 最小值	Typ. 典型值	Max. 最大值	
Static Characteristic 静态特性						
Drain to Source Breakdown Voltage 漏极-源极击穿电压	BV _{DSS}	V _{GS} =0V, I _D =100μA T _j =25°C	1200	-	-	V
Zero Gate Voltage Drain Current 栅源-漏极漏电流	I _{DSS}	V _{DS} =1200V, V _{GS} =0V T _j =25°C	-	-	100	μA
Gate to Body Leakage Current 栅极-源极漏电流	I _{GSS}	V _{GS} =22V, V _{DS} =0V	-	-	100	nA
Gate to Body Leakage Current 栅极-源极漏电流	I _{SGS}	V _{GS} =-10V, V _{DS} =0V	-	-	100	nA
Static Drain-source On Resistance 漏极-源极开通电阻	R _{DS(on)}	V _{GS} =18V, I _D =20A T _j =25°C	-	60	75	mΩ
		V _{GS} =18V, I _D =20A T _j =175°C	-	120	-	
Gate Threshold Voltage 栅极-源极阈值电压	V _{GS(th)}	V _{DS} =V _{GS} , I _{DS} =5mA T _j =25°C	2.2	3.5	4.2	V
		V _{DS} =V _{GS} , I _{DS} =5mA T _j =175°C	-	2.3	-	
Gate Resistance 栅极电阻	R _G	f=1MHz	-	9.1	-	Ω
Dynamic Characteristic 动态特性						
Input Capacitance 输入电容	C _{iss}	V _{DS} =1000V, f=1MHz, V _{GS} =0V, V _{AC} =25mV	-	1250	-	pF
Output Capacitance 输出电容	C _{oss}		-	65	-	
Reverse Transfer Capacitance 反向传输电容	C _{rss}		-	7	-	
Total Gate Charge 栅极总电荷	Q _{g(tot)}	V _{DD} =800V, I _D =20A, V _{GS} =-5/18V	-	76	-	nC
Gate-source Charge 栅-源电荷	Q _{gs}		-	20	-	
Gate-Drain Charge 栅-漏电荷	Q _{gd}		-	15	-	



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Switching Characteristic at $T_j=25^{\circ}\text{C}$ (Inductive Load)

$T_j=25^{\circ}\text{C}$ 时开关特性（电感负载）

Parameter 参数	Symbol 符号	Conditions 条件	Value 值			Unit 单位
			Min. 最小值	Typ. 典型值	Max. 最大值	
MOSFET Characteristic MOSFET 特性						
Turn-on delay time 开通延迟时间	t _{d(on)}	V _{DS} =800V, V _{GS} =-5/18V, I _D =20A, R _{G(ext)} =5Ω, L=300μH	-	16	-	ns
Rise time 上升时间	t _r		-	28	-	
Turn-off delay time 关断延迟时间	t _{d(off)}		-	54	-	
Fall time 下降时间	t _f		-	34	-	
Turn-on Switching Energy 开通损耗	E _{on}		-	890	-	uJ
Turn-off Switching Energy 关断损耗	E _{off}		-	140	-	

SOURCE-DRAIN DIODE CHARACTERISTICS

源极-漏极二极管特性

Source to Drain Diode Forward Voltage 源极-漏极正向电压	V_{SD}	$V_{GS}=-5\text{V},$ $I_{SD}=10\text{A},$ $T_j=25^{\circ}\text{C}$	-	3.3	-	V
		$V_{GS}=-5\text{V},$ $I_{SD}=10\text{A},$ $T_j=175^{\circ}\text{C}$	-	3.0	-	
Continuous Diode Forward Current 正向电流	I_S	$T_C=25^{\circ}\text{C}$	-	30	-	A
Reverse recovery time 反向恢复时间	t_{rr}	$T_j=25^{\circ}\text{C},$ $V_{GS}=-5\text{V}/18\text{V},$ $V_R=800\text{V},$ $I_{SD}=20\text{A}$ $diF/dt=400\text{A}/\mu\text{s}$	-	15	-	ns
Recovered charge 恢复电荷	Q_{rr}		-	30	-	nC
Peak reverse recovery current 反向峰值电流	I_{rrm}		-	3.5	-	A

Notes:

a: Repetitive Rating : Pulse width limited by maximum junction temperature

b: Essentially independent of operating temperature

注:

a: 重复范围：脉冲宽度受限于最大结温

b: 本质上与工作温度无关



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Electrical characteristics diagram 特性曲线

Figure 1. Output Characteristics $T_J = -55^\circ\text{C}$

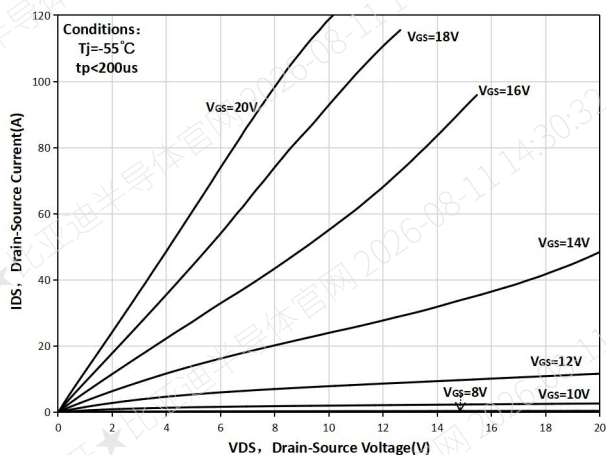


Figure 2. Output Characteristics $T_J = 25^\circ\text{C}$

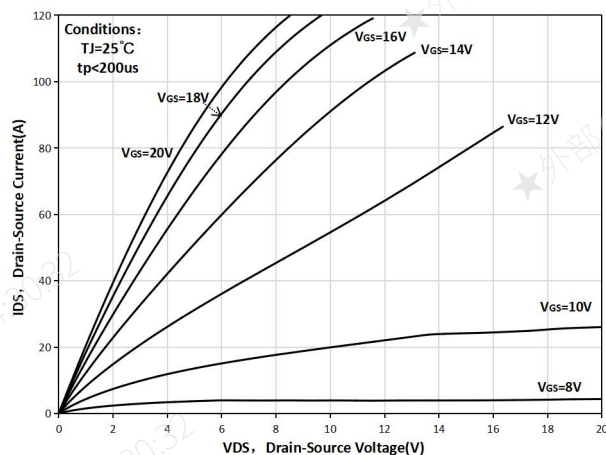


Figure 3. Output Characteristics $T_J = 175^\circ\text{C}$

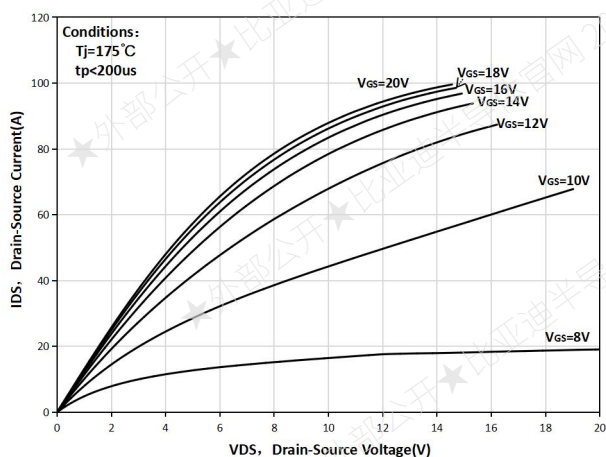


Figure 4. On-Resistance For Various Gate Voltage

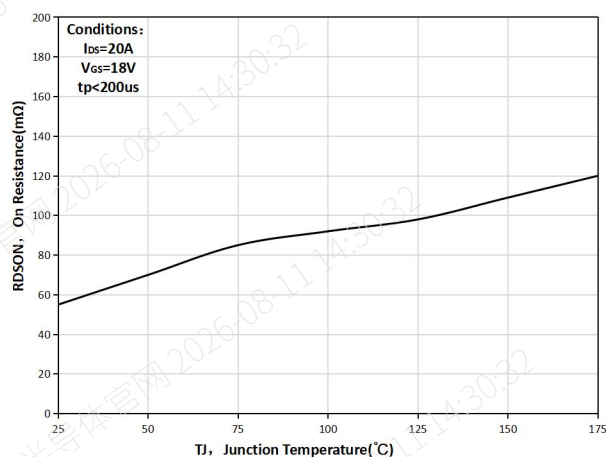


Figure 5. Transfer Characteristic
for Various Junction Temperatures

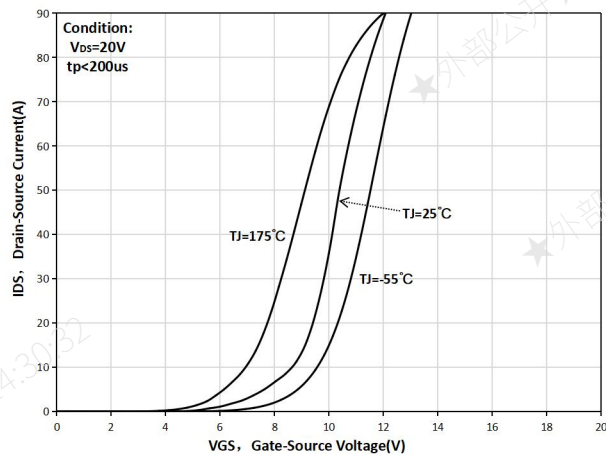
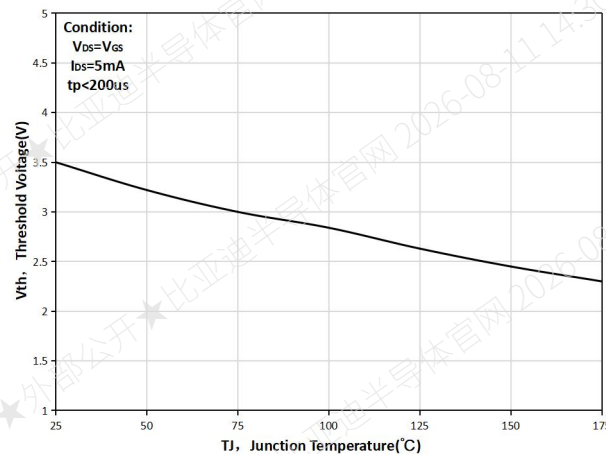


Figure 6. Threshold Voltage vs. Temperature





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Figure 7. Body Diode Characteristics at -55°C

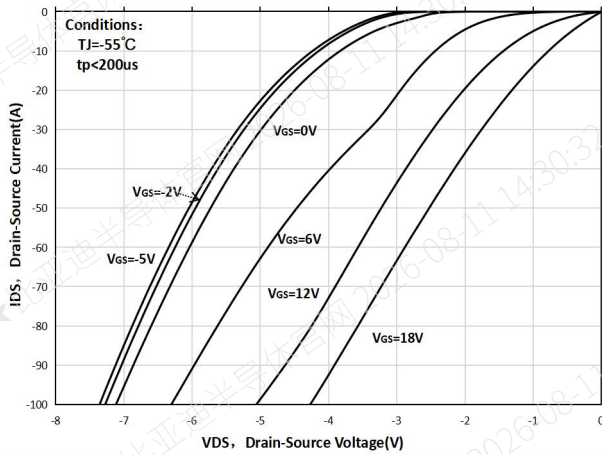


Figure 8. Body Diode Characteristics at 25°C

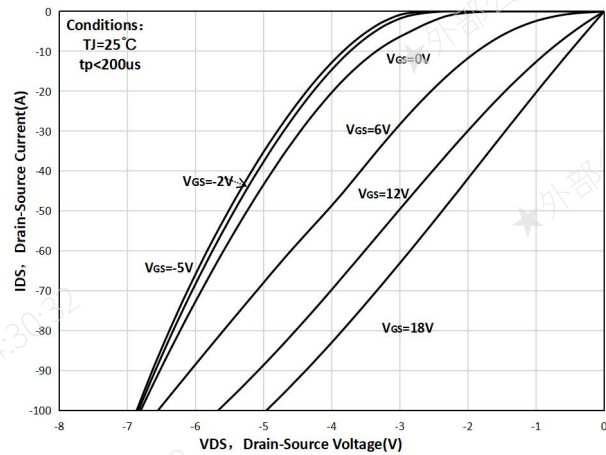


Figure 9. Body Diode Characteristics at 175°C

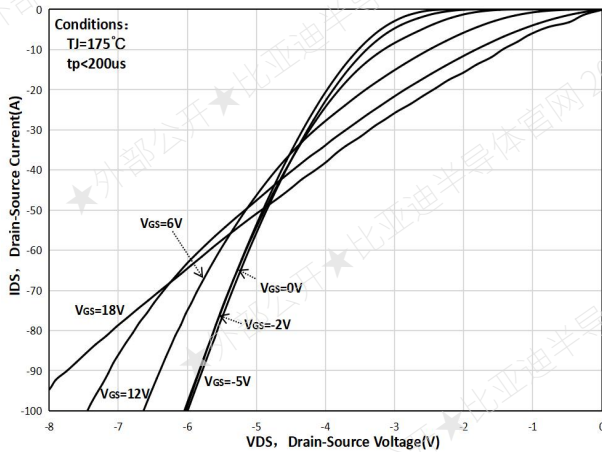


Figure 10. Capacitances vs. Drain-Source Voltage

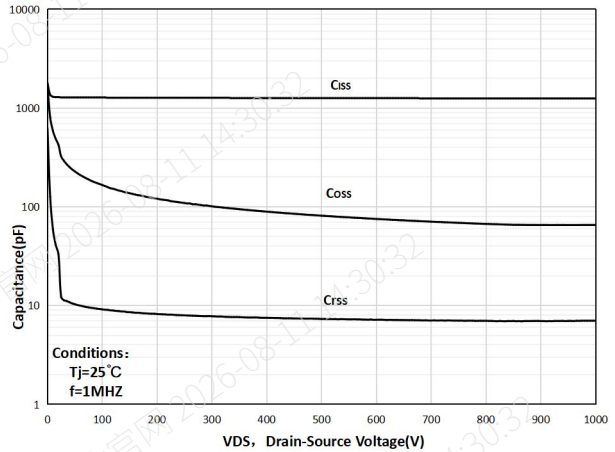


Figure 11. Gate Charge Characteristics

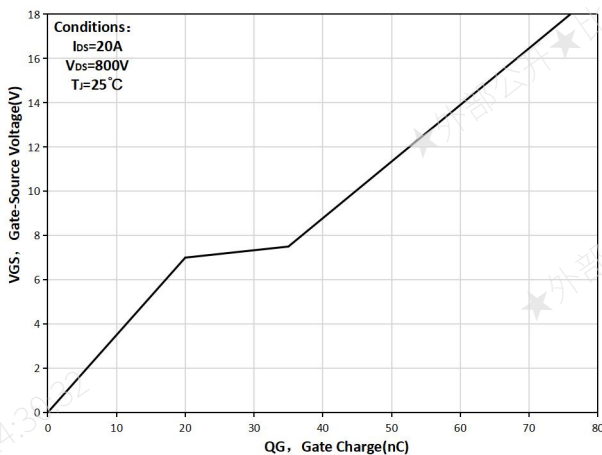
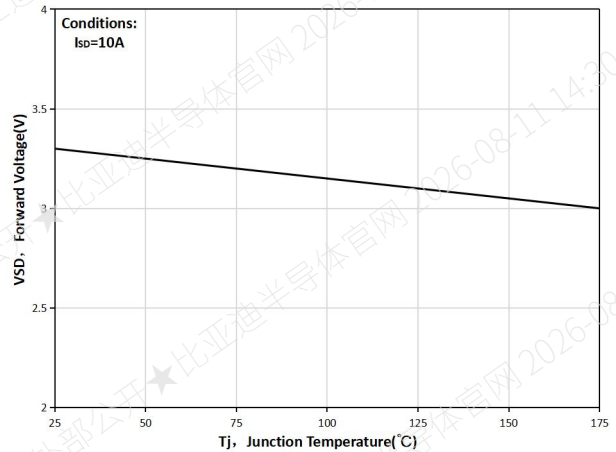


Figure 12. Forward Voltage vs. Junction Temperature





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Figure 13. Body Diode Characteristics for Various Junction Temperatures

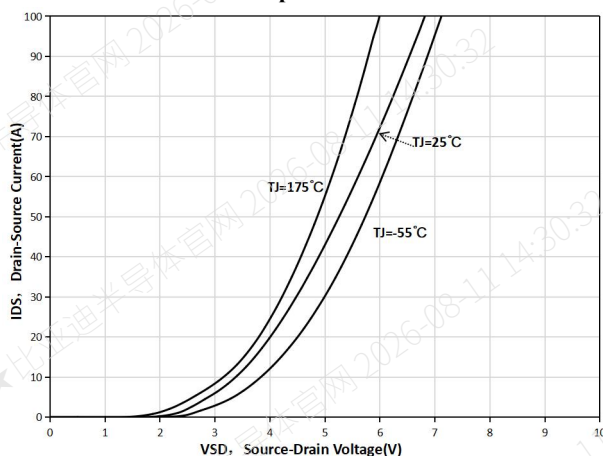


Figure 14. Clamped Inductive Switching Energy Vs. Temperature

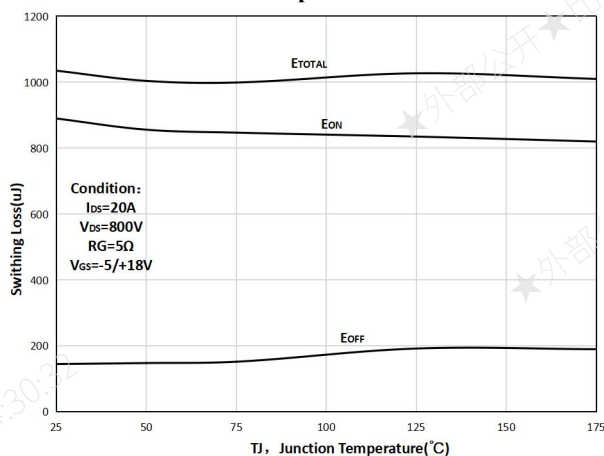


Figure 15. Switching Times vs. Junction Temperature

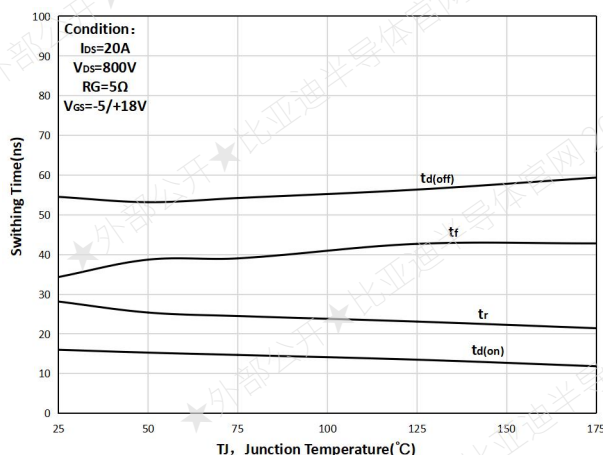


Figure 16. On-Resistance vs. Drain Current

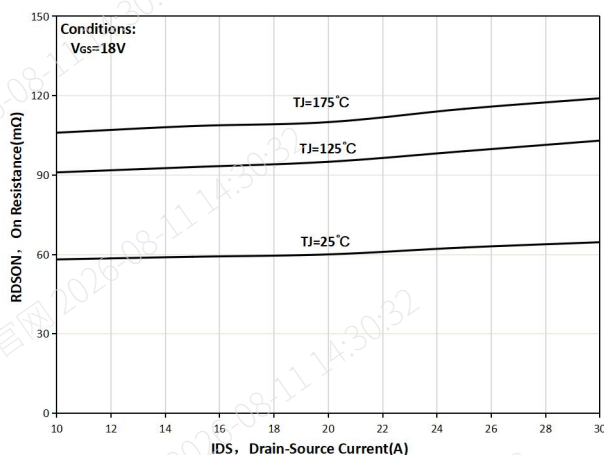


Figure 17. Continuous Drain Current Derating vs. Case Temperature

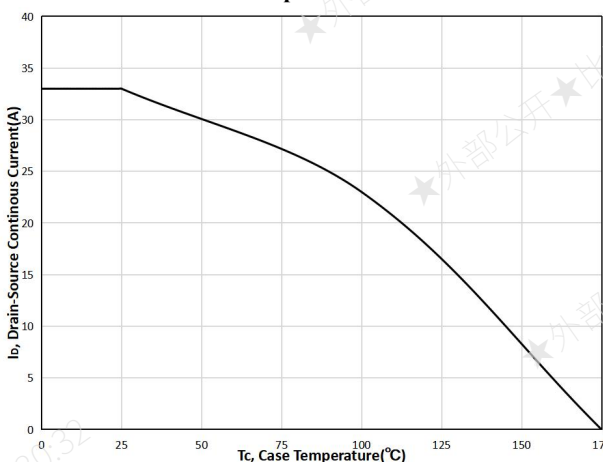
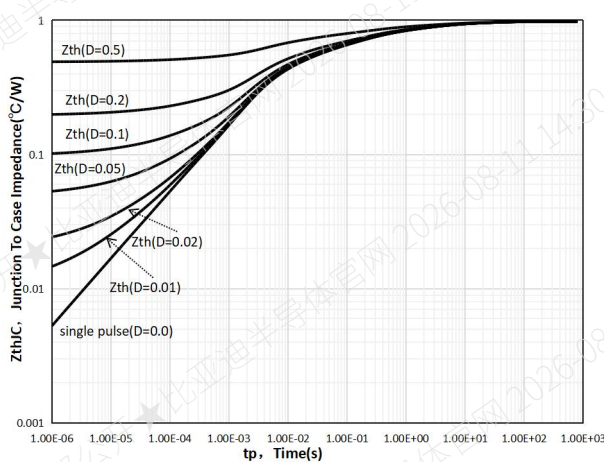


Figure 18 Transient Thermal Impedance



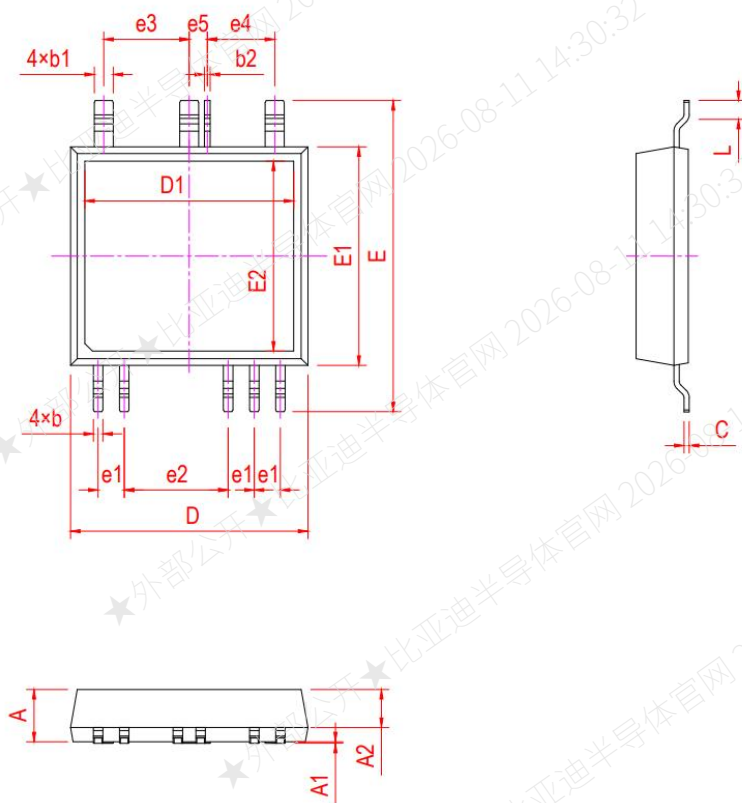


比亚迪
半导体

★外部公开★

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SOP Packing Outline Dimensions: SOP 封装外形尺寸



Dim.	Mechanical Dimensions /mm	
	MIN	MAX
A	5.40	5.60
A1	0.05	0.25
A2	3.90	4.10
b	0.90	1.10
b1	1.90	2.10
b2	0.50	0.70
c	0.45	0.60
D	24.80	25.20
D1	21.00 TYP	
E	32.40	33.00
E1	22.80	23.20
E2	19.00 TYP	
e1	2.65	2.85
e2	10.65	10.85
e3	8.50	8.70
e4	7.00	7.20
e5	2.20	2.40
L	1.05	1.45



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Special instructions: Storage Temperature: $20\pm 5^{\circ}\text{C}$; Relative Humidity: 30%-60%; The product should be stored in a place away from direct light and vibration.

质保期: 除双方在合作协议或其他书面文件中另行约定外, 产品妥当保存的情况下自购买之日起, 本规格书所述产品质保期为一年。

特殊说明: 储存温度: $20\pm 5^{\circ}\text{C}$; 相对湿度: 30%-60%; 产品应放置于避光地方, 避免震动。

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